Antiferroelectricity Driven by Cluster Jahn-Teller Effect in the Lacunar Spinel GaNb₄S₈


1Experimental Physics V, Center for Electronic Correlations and Magnetism, University of Augsburg, 86135 Augsburg, Germany
2CPM, Institute of Physics, University of Augsburg, 86135 Augsburg, Germany
3Institute of Applied Physics, MD 2028, Chisinau, Republic of Moldova
4Experimental Physics VI, Center for Electronic Correlations and Magnetism, University of Augsburg, 86135 Augsburg, Germany
5CELLS-ALBA Synchrotron, Cerdanyola del Valles, E-08290 Barcelona, Spain

We report the observation of an antiferroelectric (AFE) transition in cubic GaNb₄S₈ driven by an unconventional microscopic mechanism, the Jahn-Teller effect of Nb₄S₈ clusters. At T_{JT} = 31 K, we observed a strong drop of the dielectric constant, a clear signature of first-order AFE transitions. The first-order character is also verified by specific heat and magnetic susceptibility measurements. Below T_{JT}, the combination of single-crystal and high-resolution powder X-ray diffraction revealed a violation of the previously reported space-group P42_{1}m, in favor of a lower-symmetric distortion-pattern of the Nb₄S₈ clusters. In addition, weak ferroelectric polarization was found below T_{JT}, likely emerging due to the presence of polar domain walls within the otherwise AFE bulk structure.

Macroscopic stray fields inherent to ferromagnetic and ferroelectric orders allow coupling to uniform external fields and make these states easy to identify and control. Therefore, ferromagnetic and ferroelectric materials are extensively used in various applications, nowadays most prominently in information technology. In contrast, in antiferromagnetic and antiferroelectric (AFE) materials no macroscopic stray fields develop due to the staggered order of adjacent anti-parallel dipoles. Until the development of neutron diffraction, this hindered the direct observation of antiferroic ordering [1]. However, when it comes to memory applications, the absence of stray fields can be an advantage as it leads to the robustness of antiferroic states against unwanted switchings by disturbing macroscopic fields. In fact, the great potential of antiferromagnets in information technology has triggered an enormous progress in antiferromagnetic spintronics, a recently emerging field of magnetism [2–5].

Though antiferroelectric (AFE) compounds are also of fundamental interest and can possess similar advantages as their magnetic counterparts, this type of order is much less explored due to conceptual difficulties in defining the basic criteria of antiferroelectricity and identifying its unique experimental signatures. Beside studies on model-type perovskite antiferroelectrics [3–10] and antiferroelectricity in liquid crystals [11], there are only few reports on AFE order in other material classes [12–15].

Current approaches define antiferroelectricity via its onset: Accordingly, AFE transitions represent a class of symmetry-lowering structural transitions between two non-polar phases, upon which some of the crystallographic sites become polar [10] [19] [20]. As a clear experimental feature, the transition to the AFE state is associated with a drop of the dielectric constant [10]. In terms of symmetry, the onset of antiferroelectricity requires the point group of a symmorphic subgroup of the lower-symmetry (AFE) space group to coincide with the site symmetry of at least one of the sites which become polar upon the transition [20]. In addition, potential for an alternative polar distortion of the non-polar high-symmetry phase into a ferroelectric phase should be present [19]. If this ferroelectric state and the AFE state are separated by a sufficiently low energy barrier, a first-order transition between the two states, manifested by a double hysteresis loop of polarization versus electric field (P–E), can be driven by laboratory electric fields.

In the following, we investigate the emergence of antiferroelectricity in the AM₄X₈ lacunar spinel family, a class of cluster Mott insulators [21–23]. The lacunar spinel structure can be derived from the normal spinel structure AM₂X₄ by removing every second A-site ion.
resulting in a non-centrosymmetric but non-polar cubic structure with the space group $F\bar{4}3m$. This structure consists of two nested fcc lattices, one composed of $M_4X_4$ and the other of $AX_4$ clusters, as seen in Fig. 1(a) [24, 26]. The electronic configuration of the weakly linked $M_4X_4$ cubane clusters, within a molecular orbital scheme, leads to an unpaired electron in GaV$_4$X$_8$, and GaNb$_4$X$_8$ and an unpaired hole in GaMo$_4$X$_8$ occupying a triply degenerate cluster orbital, with $X$ being S or Se (see Fig. 1(b)) [27]. This makes the $M_4X_4$ cubic magnetic and Jahn-Teller active.

In case of GaV$_4$S$_8$, GaV$_4$Se$_8$, and GaMo$_4$S$_8$ the orbital degeneracy in the non-polar cubic phase is lifted by a ferrodistortive Jahn-Teller transition, upon which the crystal structure becomes polar, making these materials rare examples of orbital-order driven ferroelectrics [28–31]. Upon this non-polar to polar transition, taking place between 40–50 K depending on the material, all $M_4X_4$ clusters get distorted along the same cubic body diagonal, reducing the symmetry to rhombohedral (space group $R3m$) [27, 28, 30, 31]. Due to the ferrodistortive nature of the transition, the point group of the polar crystal (3m) coincides with the point group of the rhombohedrally distorted $M_4X_4$ cubane units. Recently, the electric and magnetic control of ferroelectric domain population [30, 31, 35, 36], large magnetoelectric effects [35, 37] and the formation of skyrmion lattice states [29, 35, 40] have been reported in these compounds.

In contrast, in GaNb$_4$S$_8$ the orbital degeneracy of the Nb$_4$S$_4$ units is reported to be lifted by a more complex distortion, which leads to a stronger symmetry reduction of the Nb$_4$S$_4$ units to point group $m$ [41, 42]. Still, similar to its ferrodistortive sister compounds, the main motif in the deformation of individual Nb$_4$S$_4$ clusters is an elongation parallel to one of the cubic body diagonals. This local symmetry change of the Nb$_4$S$_4$ units may give rise to the emergence of local polar moments. However, the distortion of the four adjacent Nb$_4$S$_4$ units in the unit cell is reported to be along four different cubic body diagonals, thus preventing the development of a macroscopic polarization [41, 42]. Interestingly, the tetragonal distortion in GaNb$_4$S$_8$ from space-group $F\bar{4}3m$ to space-group $P4_2\bar{1}m$ fulfills the group-theoretical criterion for AFE transitions [10, 20]: Ga is the only atom occupying a Wyckoff position with non-polar site symmetry $4\bar{3}m$ in the space-group of the cubic high-temperature phase. In the transition to the space-group of the tetragonal low-temperature phase a polar site symmetry $m$ is obtained for Ga that coincides with the point group of the $C1m1$ and $P1m1$ symmorphic subgroups of $P4_2\bar{1}m$.

To further investigate the Jahn-Teller transition and the possible emergence of antiferroelectricity in GaNb$_4$S$_8$ we apply a multi-probe approach, including dielectric spectroscopy, single-crystal and high-resolution powder X-ray diffraction, specific heat, magnetic susceptibility and pyroelectric polarization measurements. Our results evidence that the orbital degeneracy of Nb$_4$S$_4$ clusters drives a transition to a non-magnetic AFE phase at $T_{JT} = 31$ K. Pyroelectric polarization measurements indicate an additional weak ferroelectric polarization superimposed on the AFE order.

All experiments, except the powder X-ray diffraction, were performed on single-crystals grown by the chemical transport reaction method using synthesized polycrystals and iodine as the transport agent. (For experimental
details see the supplemental material [42-50].

Figs. 2(a) and (c) display reconstructions of the (hk0) reciprocal-space plane from single-crystal X-ray diffraction experiments at 42 K and 14 K, respectively. (For extended and additional reciprocal space planes see Figs. S2 and S3 [43].) On cooling below \( T_{JT} = 31 \) K, diffracted intensity was detected at positions of previously forbidden reflections of the type \( hkl : h + k, h + l, k + l = 2n + 1 \) (see Figs. 2(b) and (d)). This is compatible with the symmetry lowering from the cubic space group \( F\bar{4}3m \) to the tetragonal space group \( P42_{1}m \) reported earlier [42]. Interestingly, we found additional weak reflections at half-integer positions indicating a doubling of one unit cell axis (Fig. 2(d)). Unfortunately, unequivocal determination of the space-group was not possible. Yet, the extinction conditions observed in the single-crystal X-ray diffraction experiment can be described within space-group \( P42_{1}m \) after doubling of the c-axis. To detect potential small changes in the cell metrics that may be missed by single-crystal X-ray diffraction, we performed synchrotron powder X-ray diffraction experiments at ALBA. As shown in Fig. 2(e), below 31 K the (4,0,0) reflection splits into three peaks with nearly equal intensities, indicating that the symmetry of the low-temperature phase is not higher than orthorhombic. In contrast, the tetragonal \( P42_{1}m \) symmetry would lead to a splitting of (4,0,0) into two peaks with a 2:1 intensity ratio, which is not observed experimentally. Both single-crystal and powder XRD data are consistent with a description of the low-temperature structure of GaNbSbS<sub>8</sub> below 31 K in the non-polar but chiral orthorhombic space group \( P2_{1}2_{1}2 \). This space group choice takes into account the orthorhombic nature of the distortion seen in powder diffraction, the extinction condition \( h00, h = 2n \) and \( 0k0, k = 2n \) and the doubling of one cell-axis observed in single-crystal diffraction. It should be noted that the distortions necessitating the description in this space group are so weak that the detailed distortion pattern could not be extracted from our data.

Still it is clear that, the remaining mirror-plane symmetry of the Nb<sub>4</sub> clusters in space-group \( P42_{1}m \) is lost in space-group \( P2_{1}2_{1}2 \). Correspondingly, the site symmetry of Ga, Nb and S atoms is reduced to polar 1 coinciding with the point group of the \( P1 \) symmorphic polar subgroup of \( P2_{1}2_{1}2 \). More importantly, this retains the AFE nature of the transition from high-temperature to low-temperature phase.

To determine the temperature-dependent evolution of the structural distortion, the intensity of the \((\bar{3}, 4, 0)\) reflection, with odd \( h + k \) and \( h + l \) in violation of the symmetry-requirements of the high-temperature space-group, and the intensity of the \((4, 3.5, 0)\) reflection, indicating the cell doubling, were recorded (Fig. 3(a)). With decreasing temperature, a sudden appearance of intensity at the reflection positions is observed at \( T_{JT} \), followed by a weak gradual increase towards lower temperatures. This behavior of the reflection intensity points to an abrupt change in the structural order parameter in favor of a first-order character of the transition. In the lacunar spinels undergoing a ferroelastic-ferroelectric transition, a similar discontinuous onset of the ferroelectric polarization has been observed [28, 30, 32, 51]. An abrupt change of the lattice parameters and the cell volume as determined by high-resolution powder XRD measurements (Fig. 3(b) and Fig. S4 [43]) further supports

![FIG. 3. Temperature dependence of (a) the reflection intensities at positions \((-3, 4, 0)\) and \((4, 3.5, 0)\) as recorded by single-crystal X-ray diffraction rescaled to the same intensity level at low temperatures, (b) the lattice parameters, (c) specific heat, (d) magnetic susceptibility, and (e) dielectric constant at different frequencies. The inset in panel (d) displays the inverse susceptibility at elevated temperatures.](image-url)
the first-order nature of the transition. Also higher peak values of the \( \lambda \)-shaped anomaly on heating than on cooling of the specific heat (Fig. 3(c)), characteristic for first-order transitions and caused by the latent heat associated with the transition, can be observed.

As a key result of this work, the temperature dependence of the dielectric constant in Fig. 3(e) reveals a discontinuous, \( \sim -30\% \) decrease at \( T_{JT} \). Such a large abrupt drop of the dielectric constant has been recently identified by Toledano et al. as the primary experimental signature of first-order AFE transitions \[10, 20\]. This jump is seen at each measurement frequency, though the intrinsic plateau-like behavior of \( \varepsilon' \) above \( T_{JT} \) is masked by a gradual increase observed for low frequencies due to the Maxwell-Wagner relaxation caused by Schottky diodes forming at sample–electrode interfaces \[52, 53\]. This temperature dependence of \( \varepsilon' \) is distinct from that of the polar sister compounds, where \( \varepsilon' \) exhibits a peak at \( T_{JT} \), characteristic of ferroelectric ordering \[28, 29, 32\].

Ga\(\text{Nb}_4\)S\(_8\) is, therefore, the only so far identified orbital order driven AFE material besides Dy\(\text{VO}_4\) \[14\]. However, in the latter one the Jahn-Teller activity is caused by the electronic degeneracy in a single magnetic ion, in contrast to cluster Jahn-Teller effect present in Ga\(\text{Nb}_4\)S\(_8\).

The Jahn-Teller transition does not only have a strong impact on the polar but also on the magnetic state of Ga\(\text{Nb}_4\)S\(_8\). The sudden drop of the magnetic susceptibility at \( T_{JT} \), shown Fig. 3(c), implies that the first-order structural transition is accompanied by spin-singlet formation, as concluded from nuclear magnetic resonance studies \[50\]. (The low-temperature upturn is due to a small amount of paramagnetic impurities.) The antiferromagnetic exchange is clearly manifested in the large, negative Curie-Weiss temperature of \( \theta = -300\,\text{K} \), as determined from the fit of the inverse susceptibility in the inset of Fig. 3(c) \[11, 22\]. The strong magnetic exchange might also be one reason for the stronger symmetry reduction of Ga\(\text{Nb}_4\)S\(_8\) at \( T_{JT} \) (index of group-subgroup relation: 48) as compared to the lacunar spinels transforming to a polar low-temperature phase. In these compounds the exchange coupling is considerably weaker \((|\theta| < 50\,\text{K}) \[27, 54, 55\], giving rise to the magnetic transition well below \( T_{JT} \) and a weak rhombohedral symmetry reduction (index of group-subgroup relation: 4). A similar interlocking between the structural transition and the onset of a non-magnetic state as well as a strong symmetry reduction has been recently observed in Ga\(\text{Nb}_4\)Se\(_8\) and Ga\(\text{Ta}_4\)Se\(_8\) \[56\]. In these compounds, the spin-orbit coupling, in interplay with the Jahn-Teller effect of the \( \text{M}_2\text{Se}_4 \) clusters, was identified as the driving force of the magneto-structural transition. For these compounds, the relevance of spin-orbit coupling is clearly manifested in the strong reduction of their effective paramagnetic moments from the \( S=1/2 \) spin-only value. However, for Ga\(\text{Nb}_4\)Se\(_8\) we obtained an effective moment of \( \mu_{\text{eff}} = 1.67\mu_\text{B}/\text{f.u.} \), which is very close to the spin-only value \( (1.73\mu_\text{B}/\text{f.u.}) \). This implies the secondary role of spin-orbit physics and the dominance of the Jahn-Teller active Nb\(_4\) cluster with a single unpaired electron in driving the structural transition.

Interestingly, superimposed on the dominant AFE order, we observed weak ferroelectricity when the samples were cooled through the structural transition in poling electric fields. As shown in Fig. 3(a), the polarization develops smoothly without any singularity at \( T_{JT} \), which is typical for secondary order parameters, and saturates at \( \sim 15\,\text{K} \). Though the saturation polarization is gradually enhanced with increasing strength of the poling field, as seen in Fig. 3(b), it remains about one order of magnitude smaller than the ferroelectric polarization of the polar sister compounds, which show a discontinuous jump at \( T_{JT} \) \[28, 30, 31, 51\]. The absolute value of the polarization does not depend on the sign of the poling field, which implies the existence of domain states with opposite polarization similar to Ge\(\text{V}_4\)S\(_8\), the only ferroelectric lacunar spinel with an orthorhombic structure at low temperatures \[51\].

Weak ferroelectricity superimposed on AFE order has already been observed in several materials and ascribed to different mechanisms \[18, 37, 38\]. One possible explanation for the weak polarization in Ga\(\text{Nb}_4\)Se\(_8\) is a small canting of the AFE order caused by subtle distortions, which, however, were not resolved in our X-ray diffraction experiments and may not even be present without cooling in applied electric field. As a more likely mecha-
nism, domain walls can serve as the source of weak ferroelectricity in GaNb$_4$S$_8$. Recently, Wei et al. proved the existence of ferroelectric antiphase boundaries in non-polar PbZrO$_3$. These are due to the quadrupling of a unit cell parameter in a structural phase transition and compensate for an offset of half the enlarged unit cell parameter between adjacent domains. A related situation may be present in GaNb$_4$S$_8$, where the doubling of the c-parameter in the transition from HT to LT phase can give rise to similar antiphase boundaries. Very recently, the existence of polar antiphase domain walls in the non-centrosymmetric cubic state of lacunar spinels has been proposed. While such cubic inversion domains have not been observed in this material family yet, the same concept can be extended to the present low-symmetry case to explain the weak ferroelectricity in GaNb$_4$S$_8$. The observation of the slightly enhanced polarization with increasing cooling rate, as presented in Fig. 4(c), is in favor of such a domain-wall-related scenario. Slower cooling leads to larger domain sizes and, consequently, to a reduced number of domain walls. However, further studies are necessary to pin down the precise reason for weak ferroelectricity in this compound, e.g. by evidencing the existence of polar domain walls.

Despite the presence of weak ferroelectricity, we did not succeed with suppressing the primary AFE order and transforming the system to a ferroelectric state by either in situ or poling electric fields. This is likely due to the fact that the energy barrier separating the AFE and the potential ferro- or ferrielectric state is larger than the typical dielectric energy terms induced by fields in the range of 20 kV/cm. On the other hand, this energy barrier should not be too high, since several compounds in this family, such as GaV$_4$S$_8$, GaV$_4$Se$_8$ and GaMo$_4$S$_8$, realize a polar rhombohedral ground state. Moreover, besides the ferroic and layered antiferroic order of dipoles leading to rhombohedral and orthorhombic symmetries, respectively, an electric quadrupolar order has been recently reported in GaNb$_4$Se$_8$, where the peculiar pattern of the distortions of Nb$_2$Se$_4$ units increases the unit cell but preserves the cubic symmetry (P2$_1$3). This structural polymorphism, characteristic to lacunar spinels, implies that the primary energy gain associated with the Jahn-Teller distortion is related to the deformation of the individual M$_4$X$_4$ clusters, while the actual overall pattern of these local distortions has a minor impact on the total energy of the system.

In summary, we have performed structural, dielectric, specific heat and magnetic studies to elucidate the polar and magnetic state of the lacunar spinel GaNb$_4$S$_8$ below its Jahn-Teller transition at $T_{JT} = 31$ K. Our combined single-crystal and powder X-ray diffraction measurements revealed a structural distortion compatible with space-group $P2_12_12$ below $T_{JT}$. We demonstrate that the transition leads to the transformation of the non-polar cubic state to an AFE state, which is driven by the Jahn-Teller distortion of Nb$_4$S$_4$ clusters. In addition, we detected the emergence of a weak ferroelectric polarization below $T_{JT}$. It most likely arises from polar domain walls, which, however, needs further experimental verification. Our studies also reveal the first-order character of the AFE transition and the non-magnetic nature of the low-temperature phase. In contrast to its sister compounds exhibiting ferroelectric transitions at $T_{JT}$, GaNb$_4$S$_8$ is unique in demonstrating that cluster Jahn-Teller effect can also provide a non-canonical mechanism for the emergence of antiferroelectricity.

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* korbimian.geirhos@physik.uni-augsburg.de


[43] See Supplemental Material for experimental details, extended and additional reciprocal space planes, and temperature dependence of lattice parameters and cell volume, which includes Refs. [42, 44-49].

[44] A. Reisinger, N. Trapp, I. Krossing, S. Altmannshofer,


